

Dual N-Channel 20 V (D-S) MOSFET

| PRODUCT SUMMARY | | | |
|---------------------|----------------------------------|---------------------------------|-----------------------|
| V _{DS} (V) | R _{DS(on)} (Ω) | I _D (A) ^a | Q _g (Typ.) |
| 20 | 0.086 at V _{GS} = 4.5 V | 2.6 ^a | 5.0 nC |
| | 0.110 at V _{GS} = 2.5 V | 2.5 ^a | |
| | 0.180 at V _{GS} = 1.8 V | 2.3 ^a | |

FEATURES

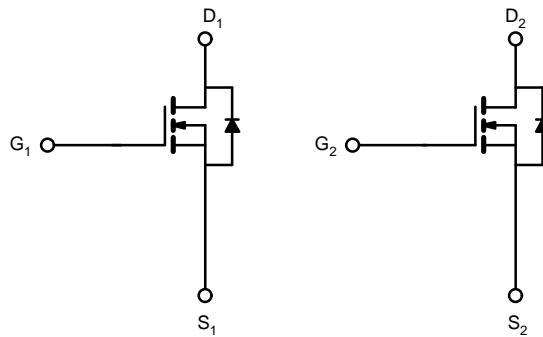
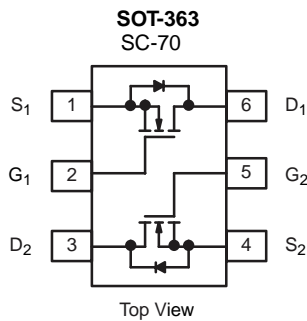
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Typical ESD Protection 2100 V HBM
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT

APPLICATIONS

- Load Switch for Portable Applications



| ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted) | | | |
|---|-----------------------------------|------------------------|------------------------|
| Parameter | Symbol | Limit | Unit |
| Drain-Source Voltage | V _{DS} | 20 | V |
| Gate-Source Voltage | V _{GS} | ± 12 | |
| Continuous Drain Current (T _J = 150 °C) | I _D | T _C = 25 °C | 2.6 ^a |
| | | T _C = 70 °C | 2.2 ^a |
| | | T _A = 25 °C | 2.3 ^{a, b, c} |
| | | T _A = 70 °C | 1.8 ^{b, c} |
| Pulsed Drain Current | I _{DM} | 8 | A |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | |
| | | T _A = 25 °C | 2.10 ^{b, c} |
| Maximum Power Dissipation | P _D | T _C = 25 °C | 2.70 |
| | | T _C = 70 °C | 1.70 |
| | | T _A = 25 °C | 1.5 ^{b, c} |
| | | T _A = 70 °C | 1.0 ^{b, c} |
| Operating Junction and Storage Temperature Range | T _J , T _{stg} | - 55 to 150 | °C |

| THERMAL RESISTANCE RATINGS | | | | | |
|---|-------------------|---------|---------|------|--|
| Parameter | Symbol | Typical | Maximum | Unit | |
| Maximum Junction-to-Ambient ^{b, d} | R _{thJA} | 130 | 170 | °C/W | |
| Maximum Junction-to-Foot (Drain) | R _{thJF} | 80 | 100 | | |

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. Maximum under steady state conditions is 220 °C/W.

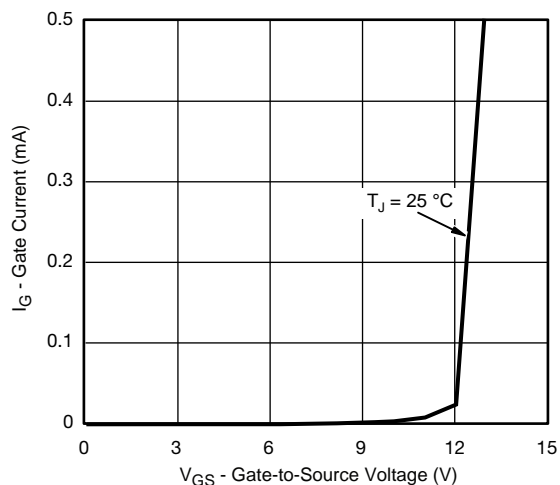
| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | |
|--|-------------------------|--|------|-------|----------|----------------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 20 | | | V |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | $I_D = 250\text{ }\mu\text{A}$ | | 20 | | mV/ $^\circ\text{C}$ |
| $V_{GS(th)}$ Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | | | -2.3 | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 0.5 | | 2.0 | V |
| Gate-Source Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$ | | | ± 25 | μA |
| | | $V_{DS} = 0\text{ V}, V_{GS} = \pm 4.5\text{ V}$ | | | 1 | |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$ | | | 10 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \leq 5\text{ V}, V_{GS} = 4.5\text{ V}$ | 4 | | | A |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = 4.5\text{ V}, I_D = 1\text{ A}$ | | 0.086 | | Ω |
| | | $V_{GS} = 2.5\text{ V}, I_D = 1\text{ A}$ | | 0.110 | | |
| | | $V_{GS} = 1.8\text{ V}, I_D = 0.2\text{ A}$ | | 0.180 | | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = 4\text{ V}, I_D = 1.5\text{ A}$ | | 4 | | S |
| Dynamic^b | | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = 10\text{ V}, V_{GS} = 8\text{ V}, I_D = 1.5\text{ A}$ | | 5.0 | | nC |
| | | $V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 1.5\text{ A}$ | | 3.0 | | |
| Gate-Source Charge | Q_{gs} | $V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 1.5\text{ A}$ | | 1.0 | | nC |
| Gate-Drain Charge | Q_{gd} | | | 2.0 | | |
| Gate Resistance | R_g | $f = 1\text{ MHz}$ | 0.4 | 1.9 | 3.8 | k Ω |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 10\text{ V}, R_L = 8.3\text{ }\Omega$ $I_D \cong 1.2\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$ | | 43 | 65 | ns |
| Rise Time | t_r | | | 80 | 120 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 480 | 720 | |
| Fall Time | t_f | | | 220 | 330 | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD} = 10\text{ V}, R_L = 8.3\text{ }\Omega$ $I_D \cong 1.2\text{ A}, V_{GEN} = 8\text{ V}, R_g = 1\text{ }\Omega$ | | 22 | 33 | ns |
| Rise Time | t_r | | | 46 | 70 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 645 | 968 | |
| Fall Time | t_f | | | 215 | 323 | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I_S | $T_C = 25\text{ }^\circ\text{C}$ | | 2.6 | | A |
| Pulse Diode Forward Current | I_{SM} | | | 4 | | |
| Body Diode Voltage | V_{SD} | $I_S = 1.2\text{ A}, V_{GS} = 0\text{ V}$ | | 0.8 | 1.2 | V |
| Body Diode Reverse Recovery Time | t_{rr} | $I_F = 1.2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$ | | 9 | 18 | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | | | 2 | 4 | nC |
| Reverse Recovery Fall Time | t_a | | | 5 | | ns |
| Reverse Recovery Rise Time | t_b | | | 4 | | |

Notes:

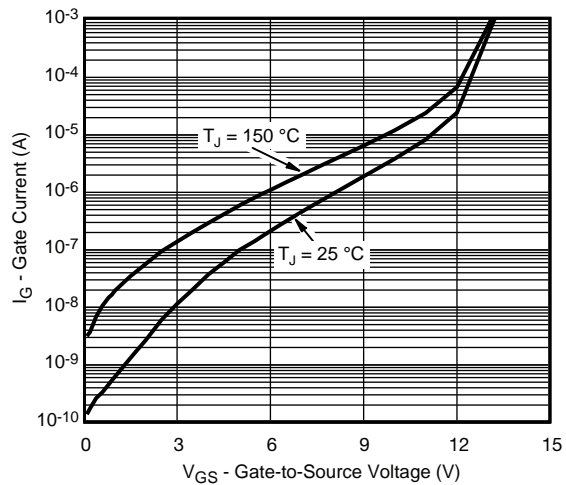
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

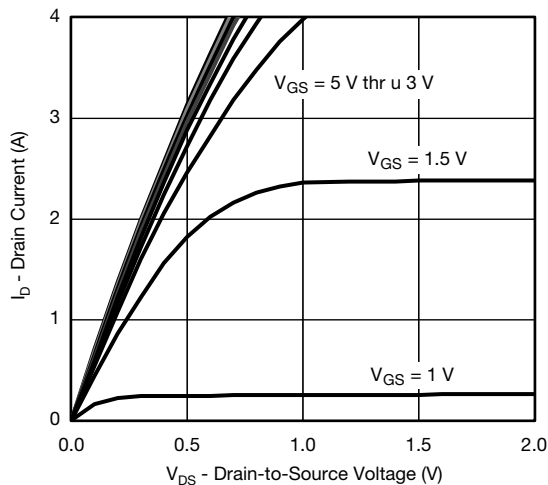
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



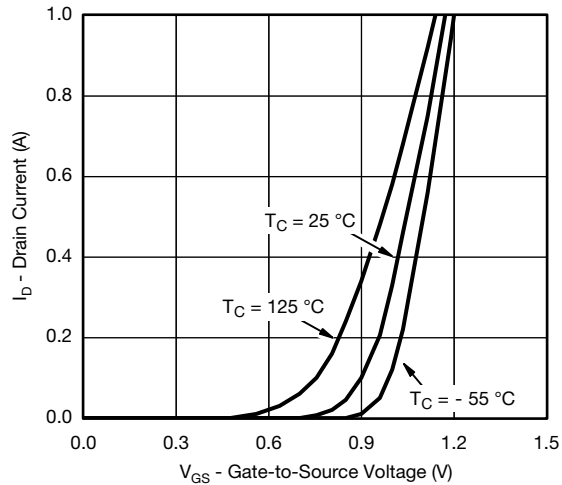
Gate Current vs. Gate-to-Source Voltage



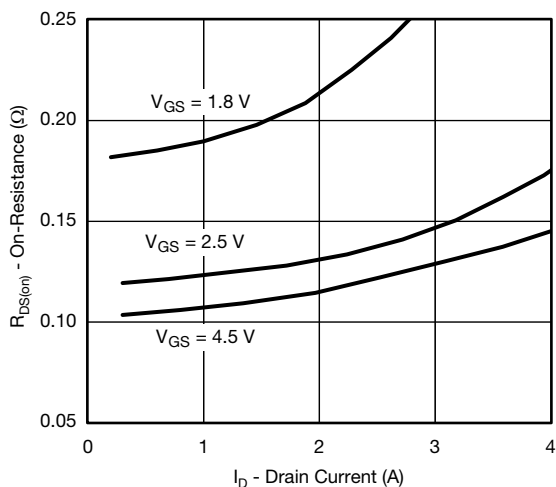
Gate Current vs. Gate-to-Source Voltage



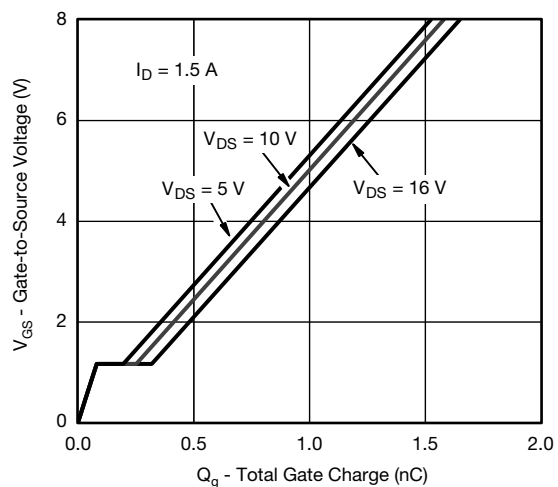
Output Characteristics



Transfer Characteristics

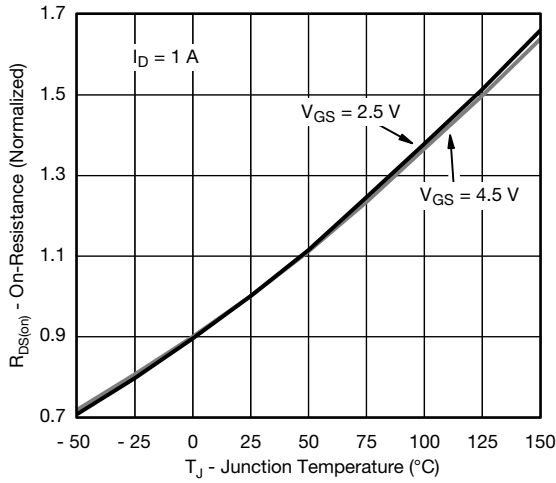


On-Resistance vs. Drain Current

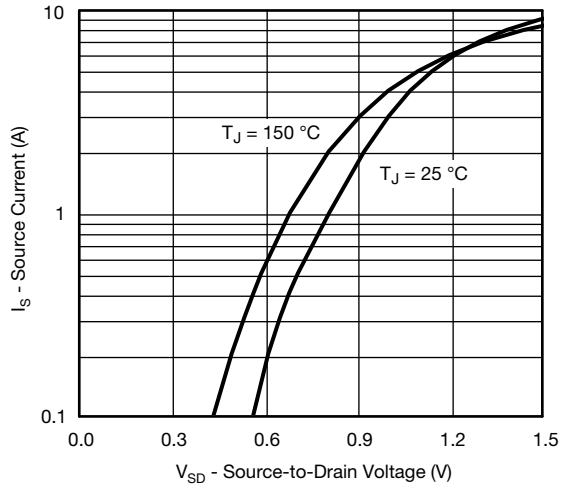


Gate Charge

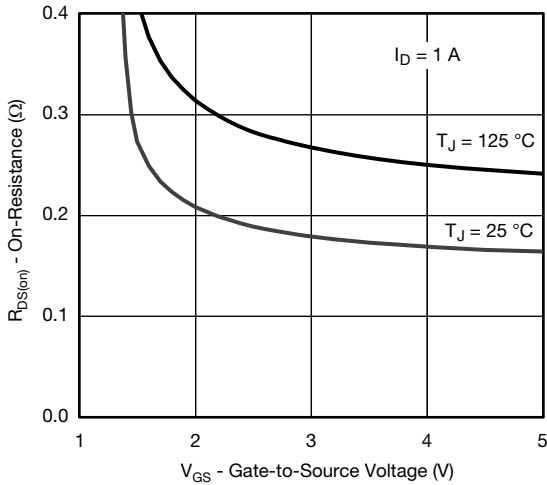
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



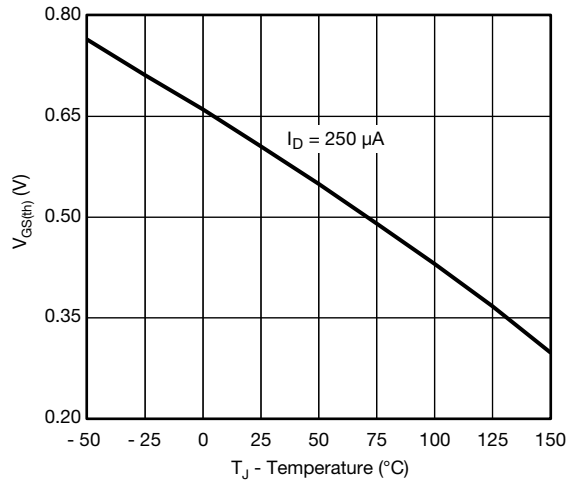
On-Resistance vs. Junction Temperature



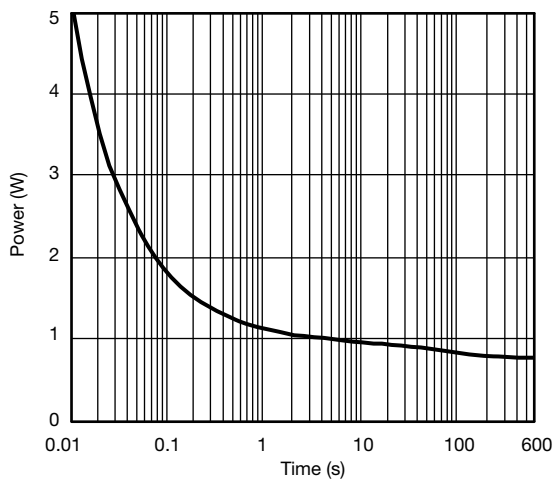
Source-Drain Diode Forward Voltage



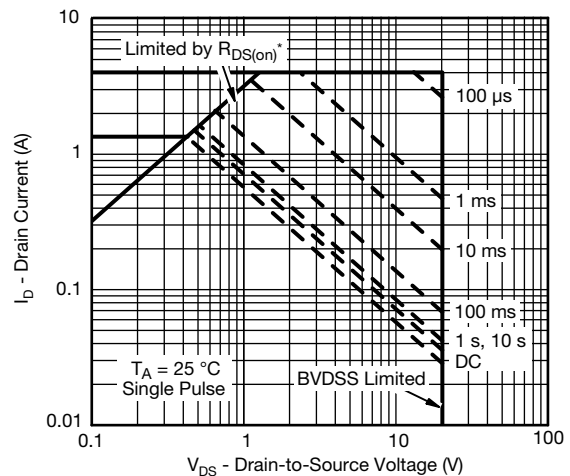
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

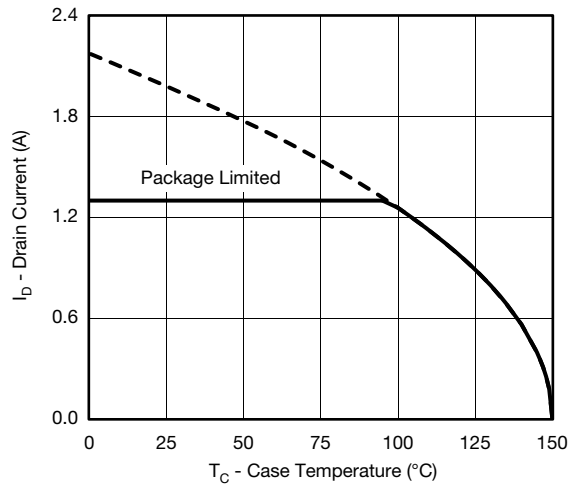


Single Pulse Power, Junction-to-Ambient

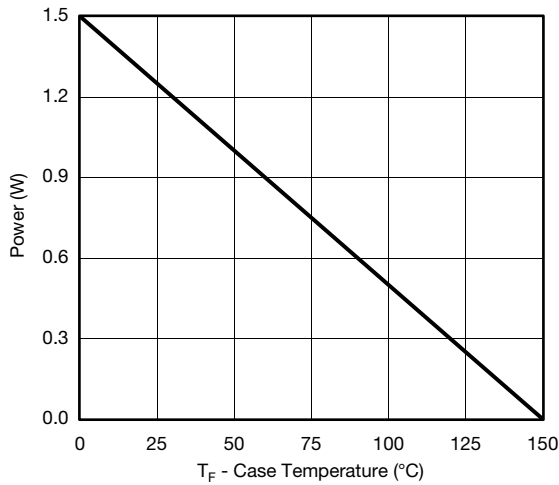


Safe Operating Area, Junction-to-Ambient
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

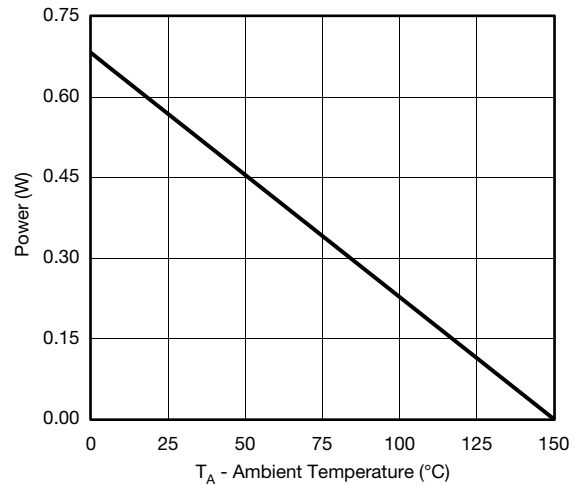
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



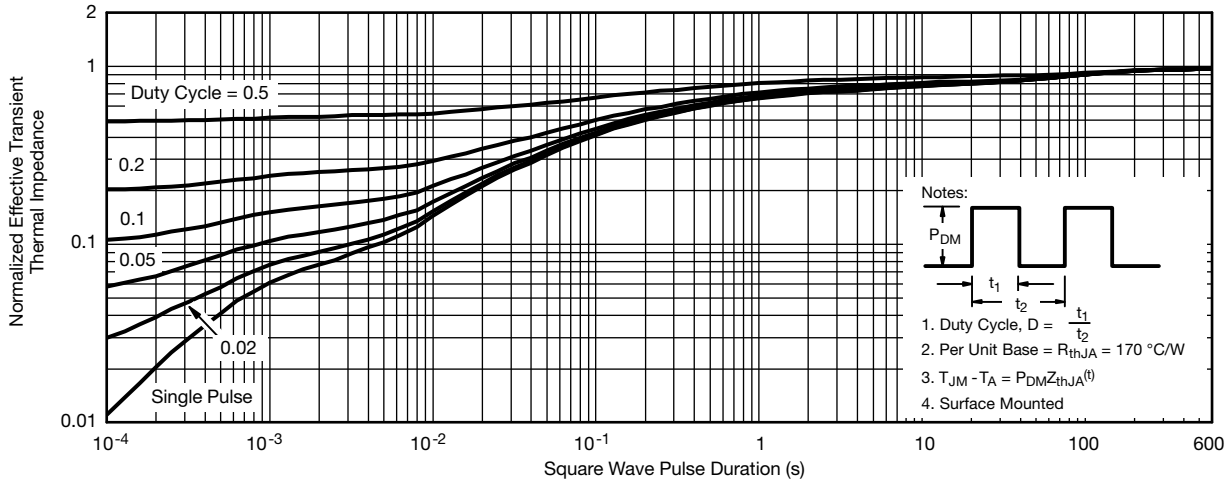
Power, Junction-to-Foot



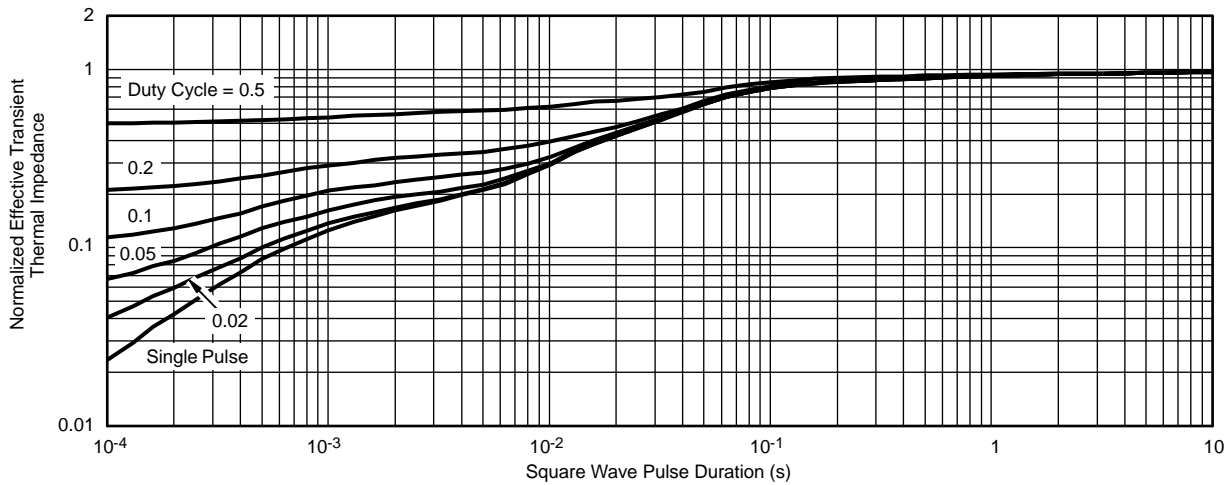
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

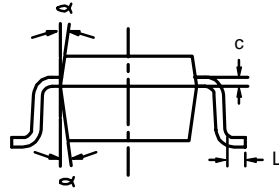
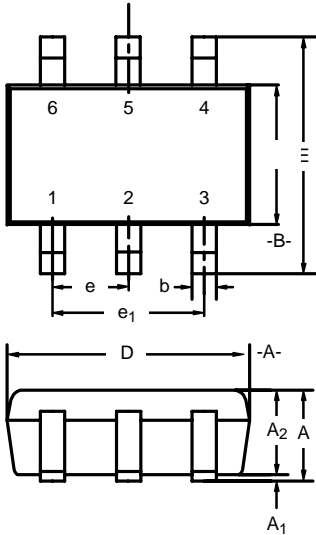


Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

SC-70: 6-LEADS



| Dim | MILLIMETERS | | | INCHES | | |
|----------------|-------------|------|------|----------|-------|-------|
| | Min | Nom | Max | Min | Nom | Max |
| A | 0.90 | - | 1.10 | 0.035 | - | 0.043 |
| A ₁ | - | - | 0.10 | - | - | 0.004 |
| A ₂ | 0.80 | - | 1.00 | 0.031 | - | 0.039 |
| b | 0.15 | - | 0.30 | 0.006 | - | 0.012 |
| c | 0.10 | - | 0.25 | 0.004 | - | 0.010 |
| D | 1.80 | 2.00 | 2.20 | 0.071 | 0.079 | 0.087 |
| E | 1.80 | 2.10 | 2.40 | 0.071 | 0.083 | 0.094 |
| E ₁ | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 |
| e | 0.65BSC | | | 0.026BSC | | |
| e ₁ | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| L | 0.10 | 0.20 | 0.30 | 0.004 | 0.008 | 0.012 |
| α | 7°Nom | | | 7°Nom | | |

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